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Complete If Known

Application Number	09/787,189
Filing Date	March 15, 2001
First Named Inventor	Slater
Group Art Unit	
Examiner Name	
Attorney Docket Number	5000.113

(use as many sheets as necessary)

Sheet	1	of	2
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**Examiner
Signature**

Shuland

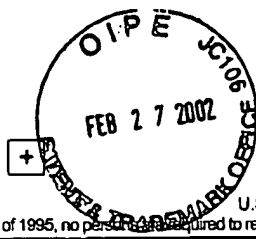
Date Considered

01/22/04

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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Compleat if Known			
		Application Number	09/787,189		
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Sheet	2	of	2	Attorney Docket Number	5000.113

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
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DV	12	SPIES (aka "Spiess"), Aluminum implantation of p-SiC for ohmic contacts, First European Conference on Silicon Carbide and Related Materials (ECSCRM 96), Oct. 6-9, 1996, pp. 1414-1419, Vol. 6, no. 10, Elsevier, Switzerland	
	13	DEV ALOK ET AL, Low Contact Resistivity Ohmic Contacts to 6H-Silicon Carbide, Proceedings of the International Electron Devices Meeting, 1993, pp. 691-694, IEEE, New York	
	14	CHEN ET AL., Contact Resistivity of Re, Pt and Ta Films on n-Type Beta-SiC: Preliminary Results, Materials Science and Engineering, 01/01/1995, pp. 165-189, Vol. B29, no. 1/03, Elsevier Sequoia, Lausanne	
DV	15	PORTER ET AL, A critical review of ohmic and rectifying contacts for silicon carbide, Materials Science and Engineering, 11-01-1995, pp. 83-105, Vol. B34, no. 2/03, Elsevier Sequoia, Lausanne	

Examiner Signature	<i>gindland</i>	Date Considered	01/22/04
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